

FLL410IK-4C

L-Band High Power GaAs FET

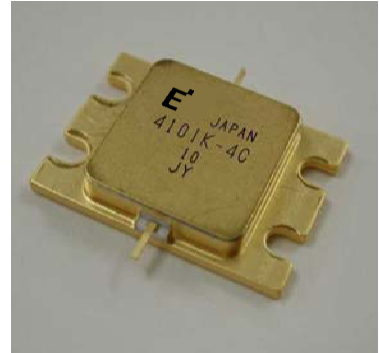
FEATURES

- High Output Power: Pout=46.0dBm(Typ.)
- High Gain: GL=11.5dB(Typ.)
- High PAE: η_{add} =44%(Typ.)
- Broad Band: 3.4~3.7GHz
- Hermetically Sealed Package

DESCRIPTION

The FLL410IK-4C is a partially matched 40 Watt GaAs FET that is designed for use in 3.4 – 3.7 GHz band amplifiers. This new product is uniquely suited for use in WLL applications as it offers excellent linearity, high efficiency, high gain, long term reliability and ease of use.

Eudyna stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATINGS (Case Temperature Tc=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	15	V
Gate-Source Voltage	V _{GS}	-5	V
Total Power Dissipation	P _T	107.0	W
Storage Temperature	T _{stg}	-65 to +175	°C
Channel Temperature	T _{ch}	175	°C

RECOMMENDED OPERATING CONDITION(Case Temperature Tc=25°C)

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V _{DS}		≤12	V
Gate Current	I _{GF}	R _G =5Ω	≤117	mA
Gate Current	I _{GR}	R _G =5Ω	≥-23	mA
Operating Channel Temperature	T _{ch}		≤145	°C

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25°C)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Drain Current	I _{DSS}	V _{DS} =5V, V _{GS} =0V	-	4.0	-	A
Pinch-off Voltage	V _p	V _{DS} =5V, I _{DS} =100mA	-0.1	-0.3	-0.5	V
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} =-1.0mA	-5.0	-	-	V
Output Power	P _{OUT}	V _{DS} =12V f=3.6 GHz I _{DS} =3A Pin=36.0dBm	45.0	46.0	-	dBm
Linear Gain *1	GL		10.5	11.5	-	dB
Drain Current	I _{dsr}		-	6.7	8.7	A
Power-added Efficiency	η_{add}		-	44	-	%
Thermal Resistance	R _{th}	Channel to Case	-	1.0	1.4	°C/W

* 1 : GL is measured at Pin=22.0dBm

CASE STYLE: IK

ESD	Class III	2000V ~
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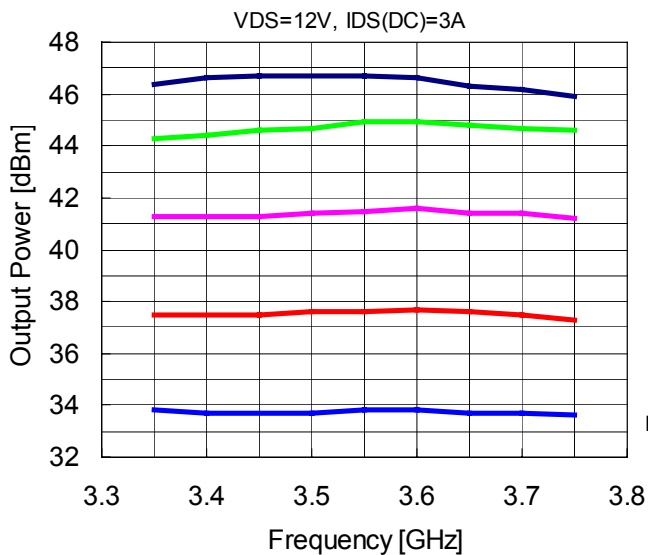
Note : Based on EIAJ ED-4701 C-111A(C=100pF, R=1.5kΩ)

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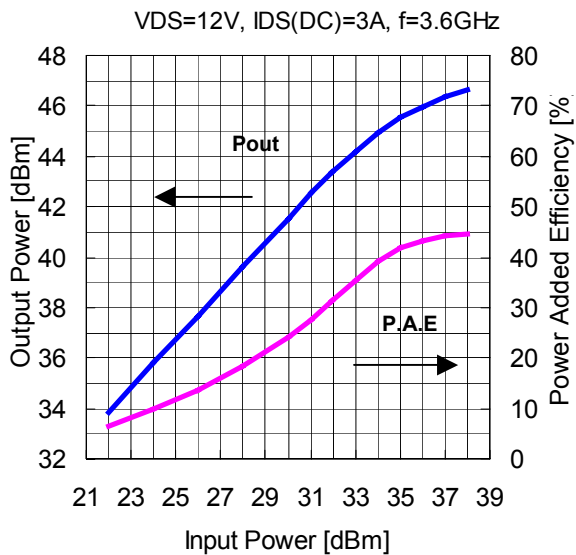
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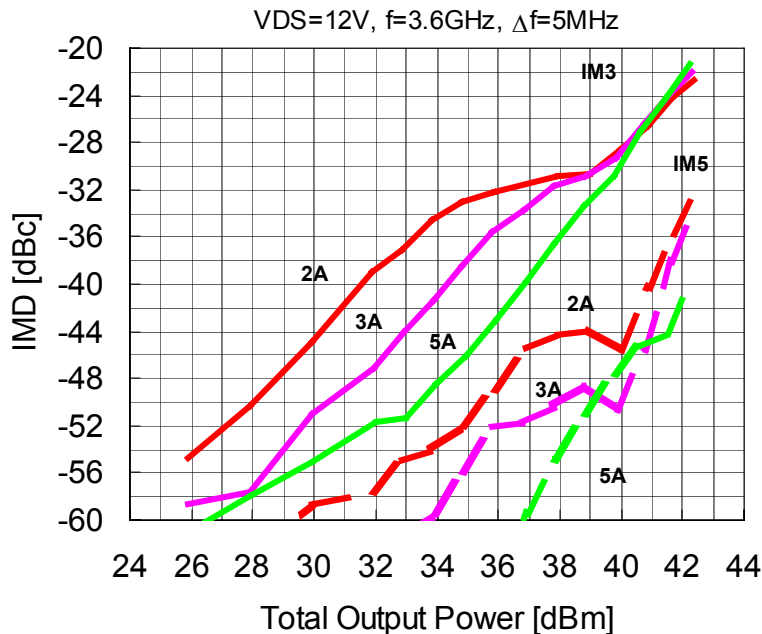
OUTPUT POWER vs. INPUT POWER



OUTPUT POWER, POWER ADDED EFFICIENCY vs. TOTAL INPUT POWER



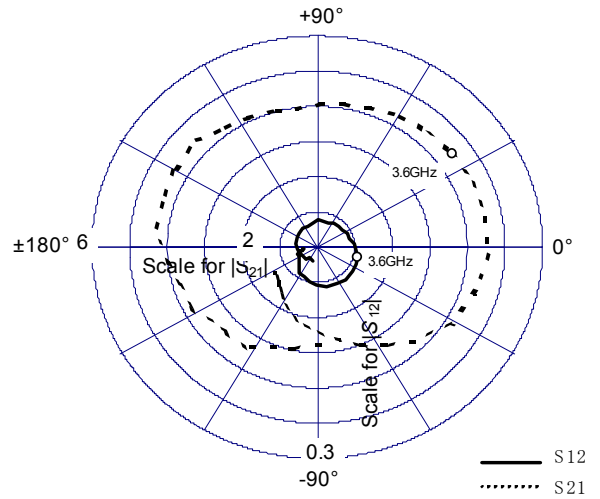
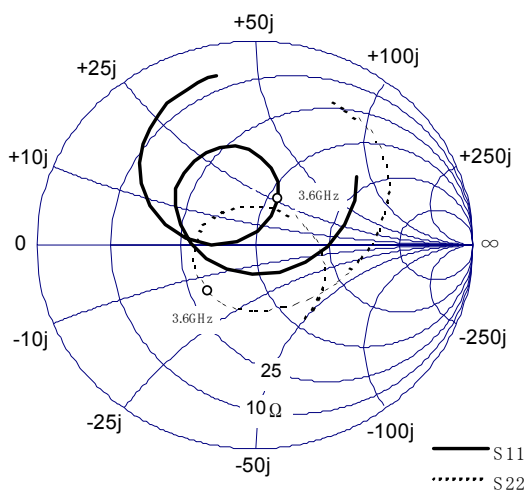
IMD vs. TOTAL OUTPUT POWER



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■ S-PARAMETER



VDS=12V, IDS=3.0A

Freq [GHz]	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2.50	0.58	35.68	2.79	-88.92	0.02	-106.81	0.79	62.67
2.60	0.42	13.30	3.06	-111.83	0.02	-133.45	0.78	52.26
2.70	0.25	-20.74	3.39	-135.39	0.02	-165.02	0.74	39.91
2.80	0.14	-94.08	3.74	-152.40	0.03	167.96	0.68	26.00
2.90	0.23	-164.13	3.98	-172.83	0.03	138.89	0.60	11.96
3.00	0.36	163.77	4.33	160.16	0.03	113.65	0.52	-2.49
3.10	0.45	142.74	4.40	136.09	0.04	88.25	0.45	-17.92
3.20	0.50	124.23	4.11	116.10	0.04	67.09	0.39	-35.62
3.30	0.50	108.29	3.94	97.42	0.04	45.57	0.34	-56.13
3.40	0.47	93.47	4.12	79.27	0.05	26.25	0.33	-79.22
3.50	0.39	78.62	4.35	59.40	0.05	5.29	0.32	-105.46
3.60	0.25	65.52	4.47	36.18	0.06	-15.70	0.32	-133.85
3.70	0.07	82.54	4.54	10.84	0.06	-37.11	0.29	-165.63
3.80	0.20	179.28	4.40	-17.44	0.06	-63.99	0.25	156.61
3.90	0.42	166.40	3.75	-46.02	0.05	-90.06	0.21	109.33
4.00	0.60	150.07	3.02	-67.67	0.05	-113.42	0.21	58.18
4.10	0.71	136.32	2.49	-86.14	0.04	-130.59	0.25	18.29
4.20	0.78	124.93	2.10	-103.97	0.03	-143.89	0.30	-8.49
4.30	0.81	115.73	1.73	-120.83	0.03	-155.27	0.36	-27.76
4.40	0.84	107.96	1.47	-133.98	0.02	-165.37	0.40	-43.35
4.50	0.85	101.79	1.34	-145.90	0.02	-172.96	0.42	-58.31

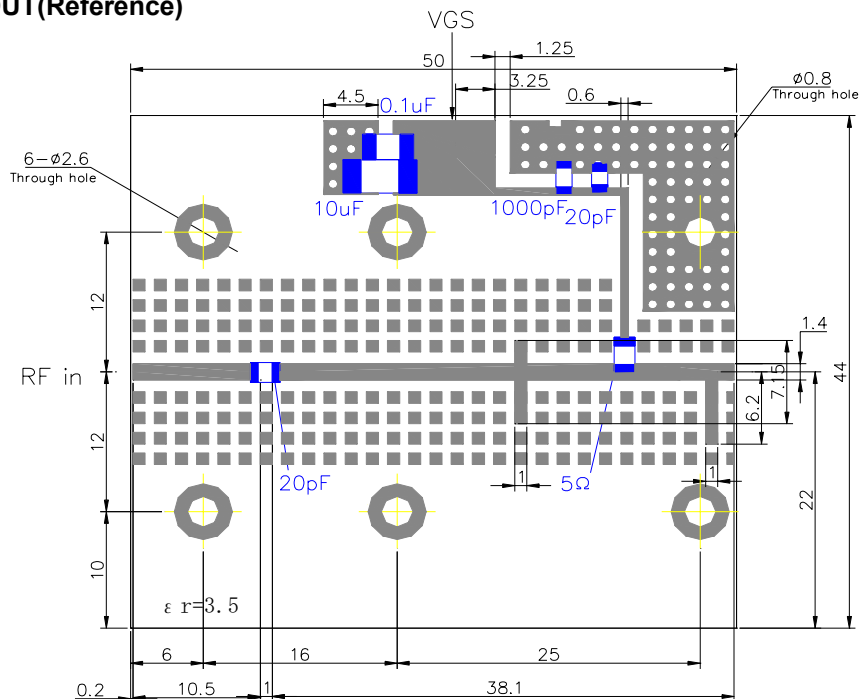
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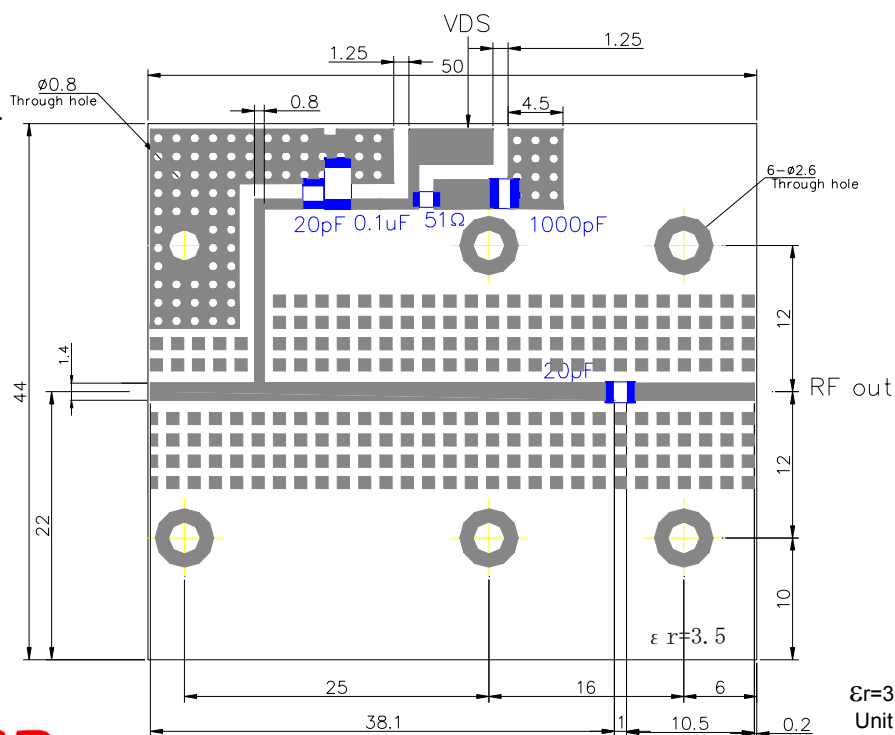
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■ BOARD LAYOUT(Reference)

<INPUT SIDE>



<OUTPUT SIDE>

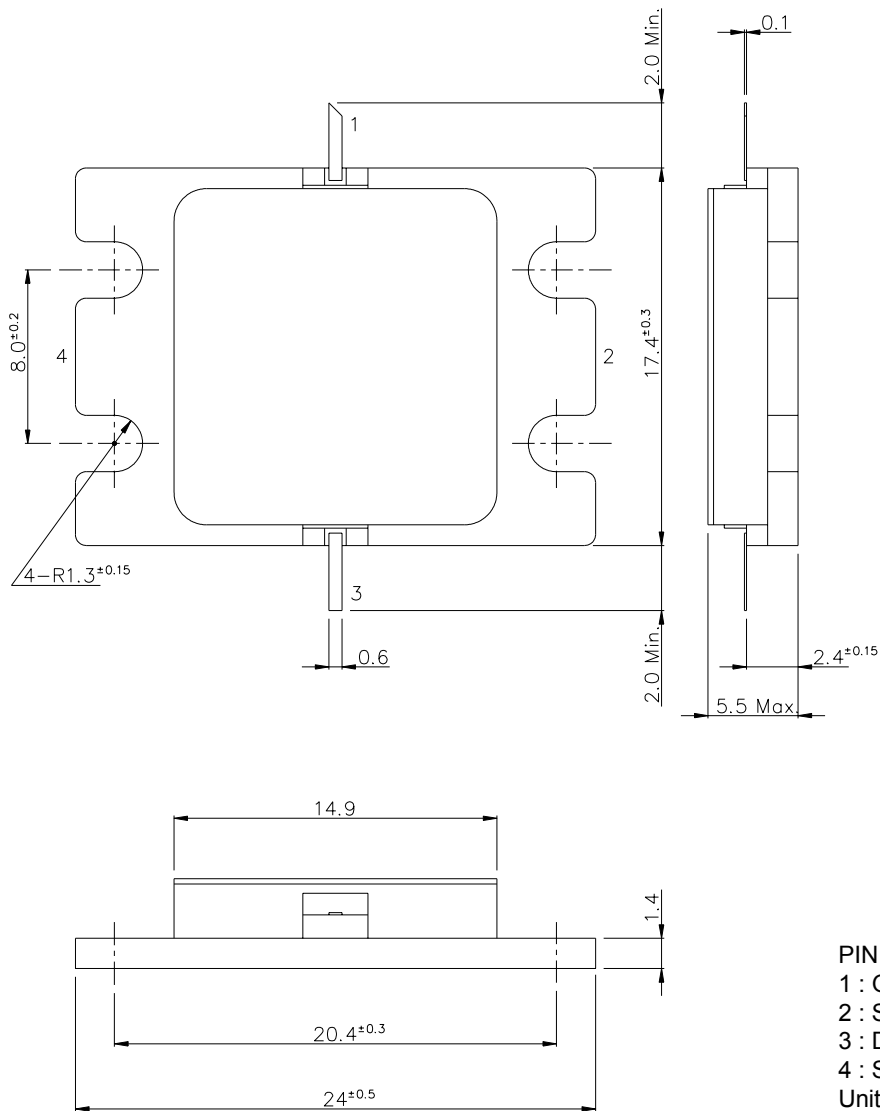
 $\epsilon_r=3.5$, $t=0.6\text{mm}$

Unit : mm

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■ Package Out Line



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